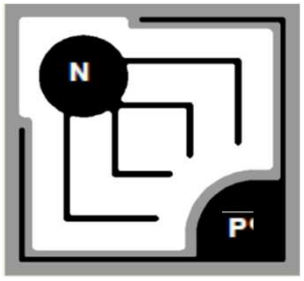
EPIGAP Optronic GmbH
Koepenicker Str. 325b
D-12555 Berlin
Fon: +49 (0)30 657637 60
Fax: +49 (0)30 657637 70
sales@epigap-optronic.de

Data Sheet

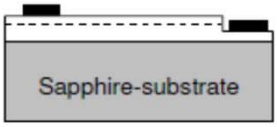
LED Chip Red — EOLC-635-34

Rev. 04, 2017

Radiation	Type	Electrodes
Red	AlGaInP / sapphire	N + P electrode up



Chip size 300 x 300 ± 25 µm
Thickness 100±15 µm
Bonding pads Ø90±10 µm
N-electrode P-electrode



Metallization electrodes: Au alloy
Transparent structure
Horizontal electrodes
Non-conductive substrate
High luminous intensity

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=20 mA	V_F	1.8		2.5	V
Reverse current	V_R=10 V	I_R			5	µA
Peak wavelength	I_F=20 mA	λ_p		635		nm
Dominant wavelength	I_F=20 mA	λ_d	619		629	nm
Spectral bandwidth at 50%	I_F=20 mA	$\Delta\lambda_{0.5}$		18		nm
Luminous intensity*	I_F=20 mA	I_V	500	600	750	mcd

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

RoHS COMPLIANT Pb-Free

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Characteristic Curves:

Fig.1 – Relative luminous Intensity vs. Forward Current

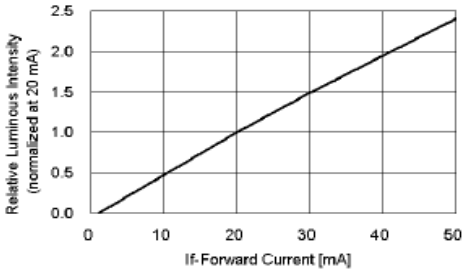


Fig.2 – Forward Current vs. Forward Voltage

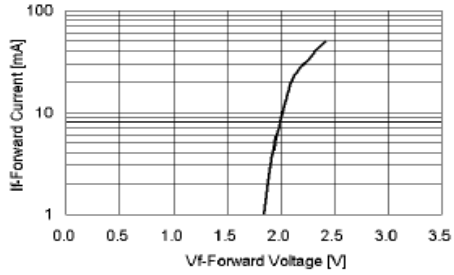


Fig.3 – Relative Intensity (@20mA) vs. Ambient Temperature

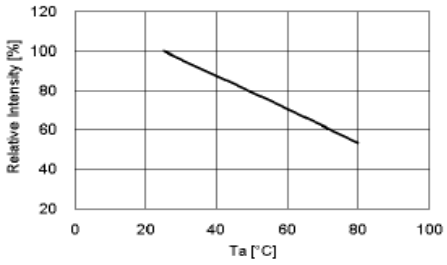


Fig.4 – Forward Voltage (@20mA) vs. Ambient Temperature

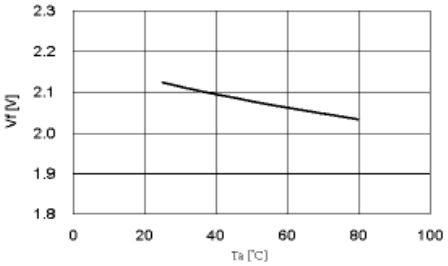


Fig.5 – Dominant Wavelength (@20mA) vs. Ambient Temperature

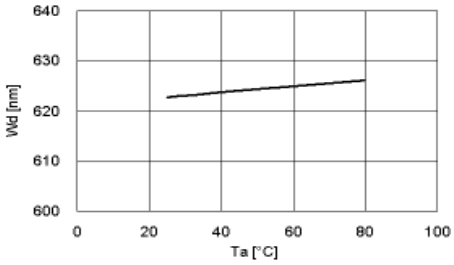
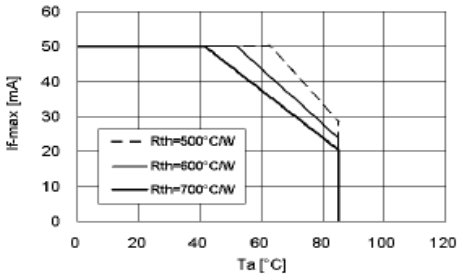


Fig.6 – Maximum Driving Forward DC Current vs. Ambient Temperature (De-rating based on Tj max. = 115°C)



Art. No. 112 017

RoHS COMPLIANT Pb-Free